

2SA1380/2SC3502

Ultrahigh-Definition CRT Display, Video Output Applications

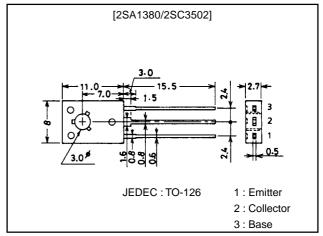
Features

- \cdot High breakdown voltage : $V_{CEO}\!\!\ge\!\!200V\!.$
- · Small reverse transfer capacitance and excellent high-frequnecy characteristics
 - : C_{re}=1.2pF (NPN), 1.7pF (PNP), V_{CB}=30V.
- · Adoption of FBET process

Package Dimensions

unit:mm

2009B



(): 2SA1380

Specifications

Absolute Maximum Ratings at Ta = 25°C

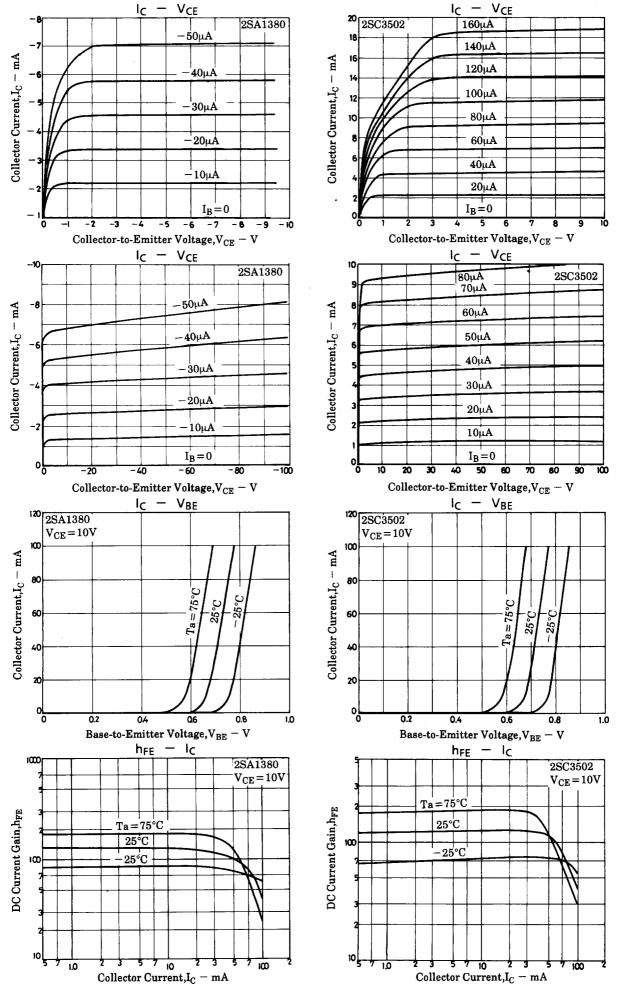
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)200	V
Collector-to-Emitter Voltage	VCEO		(-)200	V
Emitter-to-Base Voltage	V _{EBO}		(–)5	V
Collector Current	IC		(-)100	mA
Collector Current (Pulse)	I _{CP}		(-)200	mA
Collector Dissipation	PC		1.2	W
		Tc=25°C	5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

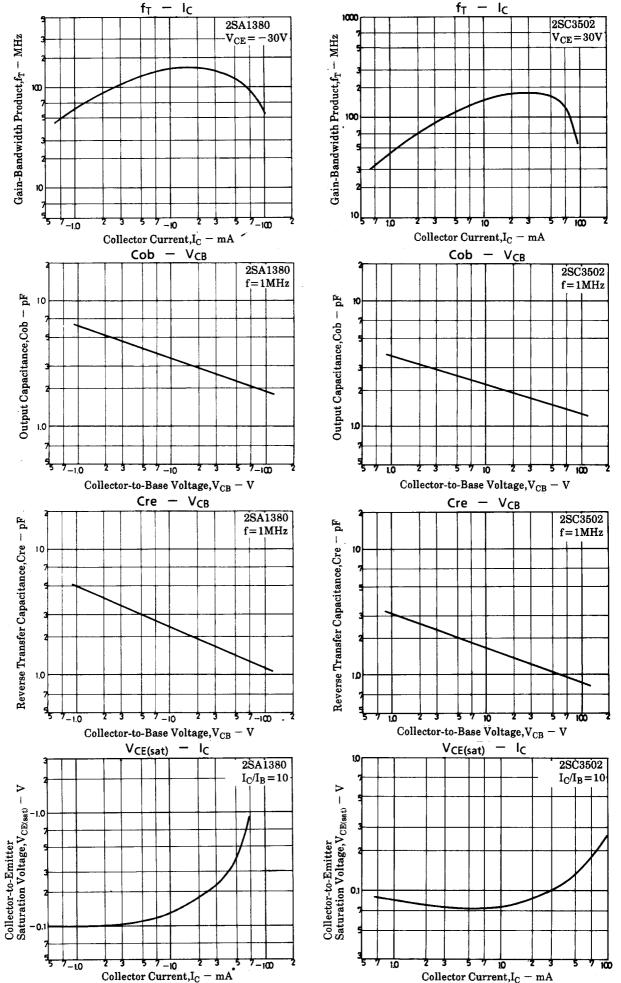
Electrical Characteristics at Ta = 25°C

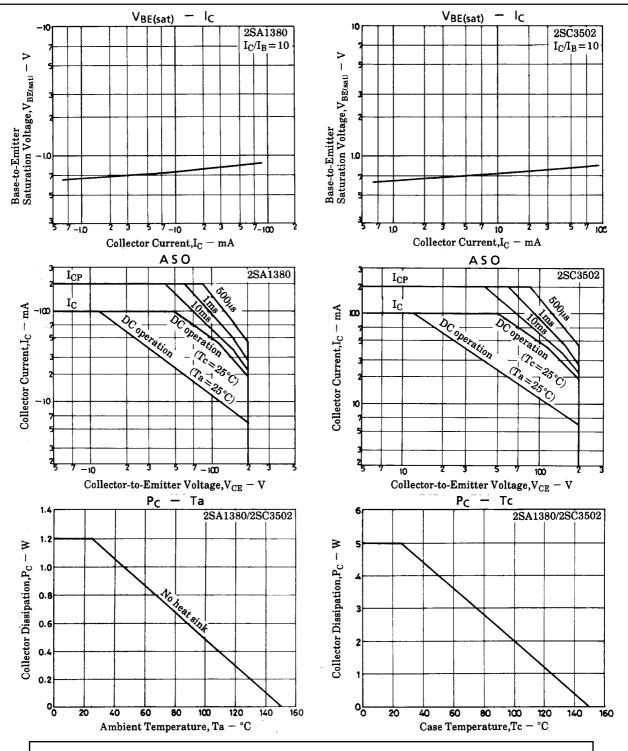
Parameter	Symbol	Conditions		Unit		
Falametei	Syllibol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)150V, I _E =0			(–)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB=} (-)4V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE}	V _{CE} =(-)10V, I _C =(-)10mA	40*		320*	
Gain-Bandwidth Product	fT	V _{CE} =(-)30V, I _C =(-)10mA		150		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)30V, f=1MHz		1.7		pF
				(2.6)		pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =(-)30V, f=1MHz		1.2		pF
				(1.7)		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)20mA, I _B =(-)2mA			(–)0.6	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)20mA, I _B =(-)2mA			(–)1.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μΑ, I _E =0	(-)200			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(-)1mA, R _{BE} =∞	(-)200			V
Emitter-to-Base Breakdown Votage	V _{(BR)EBO}	I _E =(-)10μΑ, I _C =0	(–)5			V

 $[\]ast$: The 2SA1380/2SC3502 are classified by 10mA h_{FE} as follows :

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40	С	80	60	D	120	100	Е	200	160	F	320







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